EAST Search History

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	58547	(wafer or semiconductor or substrate) near9 (dielectric or oxide or insulat$4) and (metal near9 (dielectric or oxide or insulat$4)) and ((opening or via or hole or trench or recess or aperture) near9 metal)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/04/24 07:43
L2	917	(wafer or semiconductor or substrate) near9 (dielectric or oxide or insulat$4) and (metal near9 (dielectric or oxide or insulat$4)) and ((opening or via or hole or trench or recess or aperture) near9 metal) and (stress near (relief or reliev$4))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/04/24 07:44
L3	0	(wafer or semiconductor or substrate) near9 (dielectric or oxide or insulat$4) and (metal near9 (dielectric or oxide or insulat$4)) and ((opening or via or hole or trench or recess or aperture) near9 metal) and (stress near (relief or reliev$4)) and die and (scribe near lin)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/04/24 07:44
L4	26	(wafer or semiconductor or substrate) near9 (dielectric or oxide or insulat$4) and (metal near9 (dielectric or oxide or insulat$4)) and ((opening or via or hole or trench or recess or aperture) near9 metal) and (stress near (relief or reliev$4)) and die and (scribe near line)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/04/24 08:37
L6	5237	(high near k) near (dielectric or oxide or insulat$4)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/04/24 08:38
L7	302	(high near k) near (dielectric or oxide or insulat$4) near9 (pit or recess or aperture or opening or via or hole or trench)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/04/24 08:41

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L8	69	(high near k) near (dielectric or oxide or insulat$4) near9 (pit or recess or aperture or opening or via or hole or trench) near9 (substrate or wafer or semiconductor or carrier)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/04/24 09:02
L9	10	(high near k) near (dielectric or oxide or insulat$4) near9 (pit or recess or aperture or opening or via or hole or trench) near9 (substrate or wafer or semiconductor or carrier) and stress	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/04/24 09:06
L10	42	(high near k) near (dielectric or oxide or insulat$4) near9 (pit or recess or aperture or opening or via or hole or trench) and (substrate or wafer or semiconductor or carrier) and stress	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/04/24 09:10
L11	42	(pit or recess or aperture or opening or via or hole or trench) near9 ((high near k) near (dielectric or oxide or insulat$4)) and stress	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/04/24 09:11
S1	861	(wafer or semiconductor or substrate) and dielectric and (open or via or hole or trench) and scribe and die and (metal or conduct$4)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/04 08:02
S2	872	(wafer or semiconductor or substrate) and dielectric and (opening or via or hole or trench) and scribe and die and (metal or conduct$4)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/04 08:02
S3	414	(wafer or semiconductor or substrate) and dielectric and (opening or via or hole or trench) and scribe and die and (metal or conduct$4) and stress	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/04 08:02
S4	336	(wafer or semiconductor or substrate) and dielectric and (opening or via or hole or trench) and scribe and die and (metal or conduct$4) and stress and plurality	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/04 08:02

EAST Search History

S5	272	(wafer or semiconductor or substrate) and dielectric and (opening or via or hole or trench) and scribe and die and (metal or conduct$4) and stress and plurality and expos$3	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/04 08:03
S6	206	(wafer or semiconductor or substrate) and dielectric and (opening or via or hole or trench) and scribe and die and (metal or conduct$4) and stress and plurality and expos$3 and region	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/04 08:03
S7	27	(wafer or semiconductor or substrate) and dielectric and (opening or via or hole or trench) and scribe and die and (metal or conduct$4) and stress and plurality and expos$3 and region and pit	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/04 08:19
S8	6	die and "scribe line" and (wafer or semicondcutor or substrate) and dielectric and (opening or via or hole or trench) and (metal or conduct$4) and pit	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/04 08:24
S9	43	(wafer or semicondcutor or substrate) and dielectric and (opening or via or hole or trench) and (metal or conduct$4) and pit and "scribe line"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/10 14:02
S10	6	(wafer or semicondcutor or substrate) and dielectric and (opening or via or hole or trench) and (metal or conduct$4) and pit and "scribe line" and die	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/04 12:59
S11	194	((wafer or semiconductor or substrate) near4 die) and (dielectric or oxide or insulat$4) and (via or hole or trench) and (copper or tungsten) and (metal or polysilicon) and groove and photolithograph$8 and etch	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/10 14:05
S12	20	((wafer or semiconductor or substrate) near4 die) and (dielectric or oxide or insulat$4) and (via or hole or trench or open$3) and (copper or tungsten) and (metal or polysilicon) and groove and photolithograph$8 and etch and (scribe near4 line)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/10 14:06

S13	0	((wafer or semiconductor or substrate) near4 die) and (dielectric or oxide or insulat$4) and (via or hole or trench or open$3) and (copper or tungsten) and (metal or polysilicon) and groove and photolithograph$8 and etch and (scribe near4 line) and pit	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/10 14:13
S14	27	((wafer or semiconductor or substrate) near4 die) and (dielectric or oxide or insulat$4) and (via or hole or trench or open$3) and (copper or tungsten) and (metal or polysilicon) and groove and photolithograph$8 and etch and pit	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/10 14:15
S15	15	((wafer or semiconductor or substrate) near4 die) and (dielectric or oxide or insulat$4) and (via or hole or trench or open$3) and (copper or tungsten) and (metal or polysilicon) and groove and photolithograph$8 and etch and pit and stress	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/14 07:19
S16	33326	(stress near4 (wafer or semiconductor or substrate))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/10 14:17
S17	787	((stress near4 (wafer or semiconductor or substrate)) near4 die)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/10 14:17
S18	480	(die near8 (wafer or semiconductor or substrate)) and (dielectric or oxide or insulat$4) and (open$3 or via or hole or trench or groove) and pit$2 and (photolithographic$4 or etch$4) and plug and (metal or conduct$4 or polysilicon)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/14 07:24
S19	70	(die near8 (wafer or semiconductor or substrate)) and (dielectric or oxide or insulat$4) and (open$3 or via or hole or trench or groove) and pit$2 and (photolithographic$4 or etch$4) and plug and (metal or conduct$4 or polysilicon) and (scribe near line)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/14 07:25

S20	63	(die near8 (wafer or semiconductor or substrate)) and (dielectric or oxide or insulat$4) and (open$3 or via or hole or trench or groove) and pit$2 and (photolithographic$4 or etch$4) and plug and (metal or conduct$4 or polysilicon) and (scribe near line) and (tungsten or copper)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/11/21 12:22
S21	21542	(die near9 (wafer or semiconductor or substrate)) and ((insulat$4 or oxide or dielectric) near9 (wafer or semiconductor or substrate))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/11/21 12:23
S22	197081	((die or circuit) near9 (wafer or semiconductor or substrate)) and ((insulat$4 or oxide or dielectric) near9 (wafer or semiconductor or substrate))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/11/21 12:24
S23	733	((die or circuit) near9 (wafer or semiconductor or substrate)) and ((insulat$4 or oxide or dielectric) near9 (wafer or semiconductor or substrate)) and (scribe near9 die)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/11/21 12:24
S24	30	((die or circuit) near9 (wafer or semiconductor or substrate)) and ((insulat$4 or oxide or dielectric) near9 (wafer or semiconductor or substrate)) and (scribe near9 die) and ((metal or(dielectric or oxide or insulat$4)) near9 (pit or recess))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/11/21 12:26
S25	12	((die or circuit) near9 (wafer or semiconductor or substrate)) and ((insulat$4 or oxide or dielectric) near9 (wafer or semiconductor or substrate)) and (scribe near9 die) and ((metal or(dielectric or oxide or insulat$4)) near9 (pit or recess)) and ((opening or via or hole or trench) near9 (dielectric or oxide or insulat$4))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/04/19 13:15

S26	3	((die or circuit) near9 (wafer or semiconductor or substrate)) and ((insulat$4 or oxide or dielectric) near9 (wafer or semiconductor or substrate)) and (scribe near9 die) and ((metal or(dielectric or oxide or insulat$4)) near9 (pit or recess)) and ((opening or via or hole or trench) near9 (dielectric or oxide or insulat$4)) and stress	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/11/21 13:23
S27	19949	stress near4 (dielectric or oxide or insulat$4)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/11/21 13:24
S28	162	(stress near4 (dielectric or oxide or insulat$4)) near9 fill	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/11/21 13:25
S29	85	(stress near4 (dielectric or oxide or insulat$4)) near9 fill near9 (via or hole or trench or opening)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/11/21 13:25
S30	12	(stress near4 (dielectric or oxide or insulat$4)) near9 fill near9 (via or hole or trench or opening) near9 (substrate or semiconductor or wafer)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/11/21 13:26
S31	58483	(stress near9 (wafer or semiconductor or substrate))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/04/19 11:38
S32	29190	(stress near9 (wafer or semiconductor or substrate or carrier)) and ((dielectric or oxide or insulat$4) near9 (wafer or semiconductor or substrate or carrier))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/04/19 11:40

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S33	33790	(High near stress)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/04/19 11:40
S34	451	(High near stress) near4 (dielectric or oxide or insulat$4)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/04/19 11:41
S35	54	(High near stress) near4 (dielectric or oxide or insulat$4) near9 (substrate or wafer or carrier or semiconductor)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/04/19 12:09
S36	0	(High near stress) near4 (dielectric or oxide or insulat$4) near9 (substrate or wafer or carrier or semiconductor) and (scribe near4 line)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/04/19 11:42
S37	0	(High near stress) near4 (dielectric or oxide or insulat$4) near9 (substrate or wafer or carrier or semiconductor) and (scribe near9 line)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/04/19 11:42
S38	4	(High near stress) near4 (dielectric or oxide or insulat$4) near9 (substrate or wafer or carrier or semiconductor) and pit	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/04/19 12:08
S39	3	(High near stress) near4 (dielectric or oxide or insulat$4) near9 (substrate or wafer or carrier or semiconductor) near9 (recess or pit or aperture or hole or via or trench)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/04/19 12:15
S40	19	(High near stress) near4 (dielectric or oxide or insulat$4) near9 (recess or pit or aperture or hole or via or trench)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/04/19 12:32

S41	17	"high stress dielectric"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/04/19 12:33
S42	0	(pit or hole or recess or via or opening or aperture) near9 "high stress dielectric"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/04/19 12:34
S43	0	(pit or hole or recess or via or opening or aperture or trench) near9 "high stress dielectric"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/04/19 12:35
S44	5221	(high near k) near (dielectric or oxide or insulat$4)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/04/19 12:36
S45	302	(high near k) near (dielectric or oxide or insulat$4) near9 (via or hole or recess or aperture or trench or opening)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/04/19 12:37
S46	302	(high near k) near (dielectric or oxide or insulat$4) near9 (via or hole or recess or aperture or trench or opening or pit)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/04/19 12:37
S47	0	(high near k) near (dielectric or oxide or insulat$4) near9 pit	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/04/19 12:37
S48	9	(high near k) near (dielectric or oxide or insulat$4) near9 (via or hole or recess or aperture or trench or opening or pit) and (stress near9 relie$4)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/04/19 12:38

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S49	9	(high near k) near (dielectric or oxide or insulat$4) near9 (via or hole or recess or aperture or trench or opening or pit) and (stress near9 (relief or reliev$4))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/04/19 12:48
S50	18	(high near k) near (dielectric or oxide or insulat$4) near9 (via or hole or recess or aperture or trench or opening or pit) and (stress near9 (wafer or substrate or semiconductor carrier))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/04/19 13:01
S51	98	(high near stress) near (dielectric or oxide or insulat$4)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/04/19 13:03
S52	2	(high near stress) near (dielectric or oxide or insulat$4) near9 (pit or trench or hole or aperture or recess or opening)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/04/19 13:04
S53	42	(stress near (relief or reliev$4)) and (semiconductor or substrate or wafer or carrier) near9 (dielectric or oxide or insulat$4) and die and (scribe near line) and (metal near9 (dielectric or oxide or film))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/04/19 13:18
S54	24	(stress near (relief or reliev$4)) and (semiconductor or substrate or wafer or carrier) near9 (dielectric or oxide or insulat$4) and die and (scribe near line) and (metal near9 (dielectric or oxide or film)) and ((opening or hole or aperture or recess or via or trench) near9 metal)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/04/19 13:19